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View Online at https://aerobasegroup.com/nsn/5961-01-118-9351 **Inclosure Material:** Metal **Overall Length:** 0.450 inches **Function For Which Designed:** Switching **End Application:** 1055-01-092-0596 18876 fscm **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.667 inches and 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 breakdown voltage, dc **Current Rating Per Characteristic:** 300.00 amperes repetitive peak forward current **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius ambient air **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud **Specification Data:** 81349-mil-s-19500/308 government specification Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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